



N-Channel and N-Channel Complementary MOSFET

Product Summary

- V_{DS} 50V
- I_D 300mA
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 1100m Ω
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) 1200m Ω

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface TTL/CMOS

■ Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	
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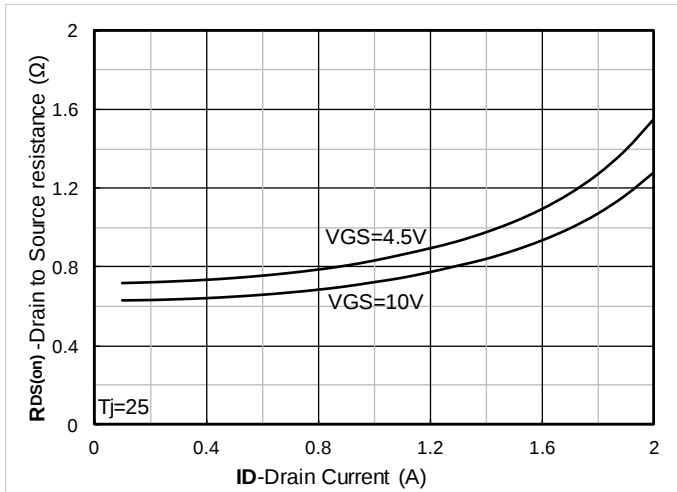


Figure 7. $R_{DS(on)}$ VS Drain Current

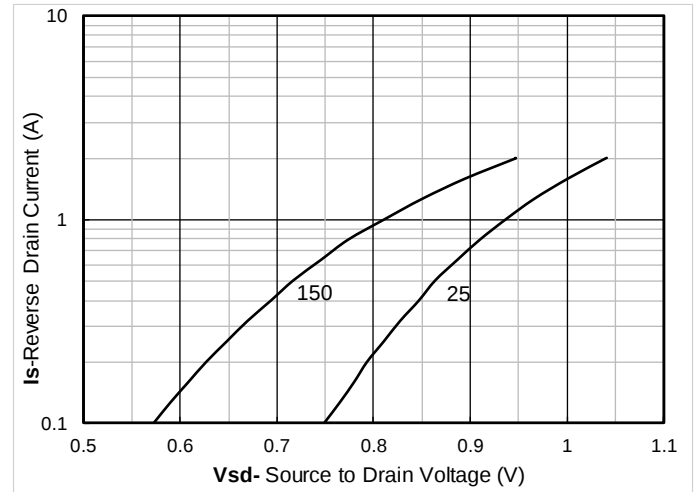


Figure 8. Forward characteristics of reverse diode

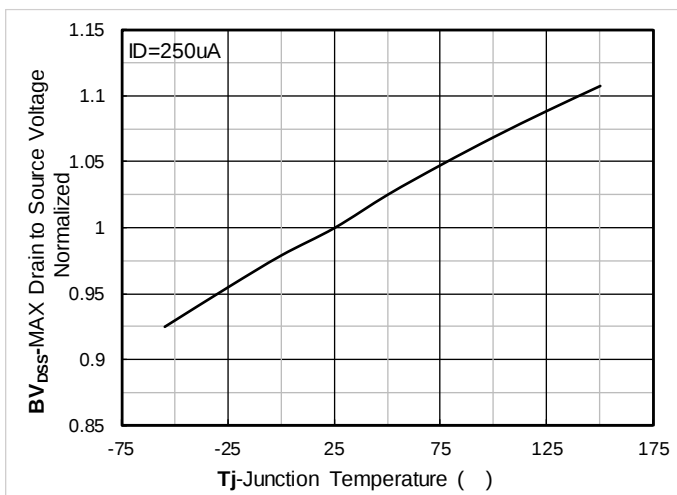


Figure 9. Normalized breakdown voltage

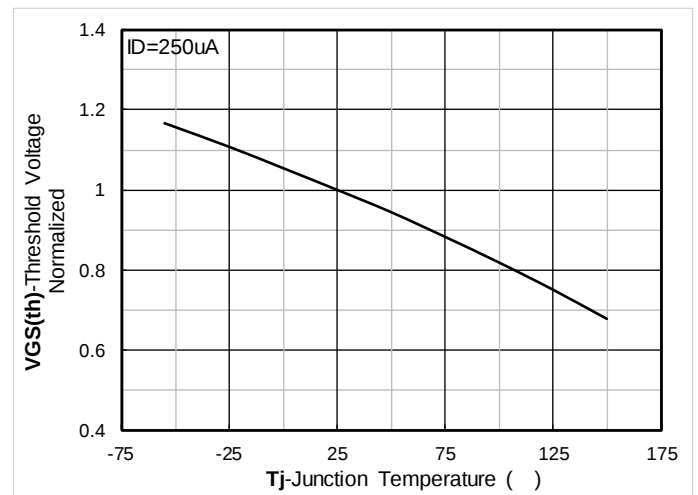


Figure 10. Normalized Threshold voltage

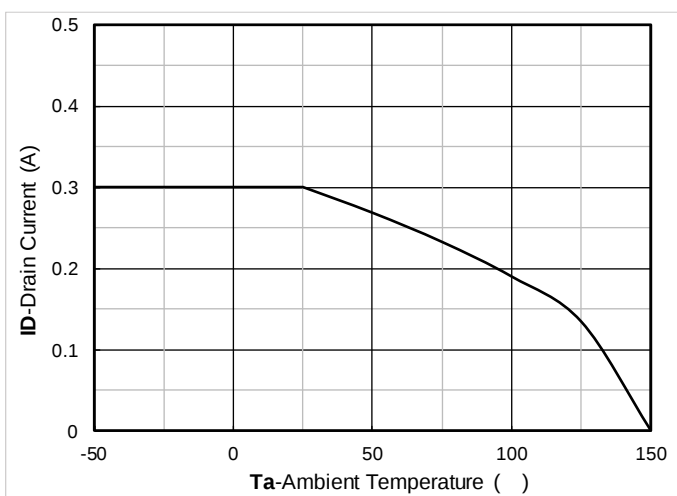


Figure 11. Current dissipation

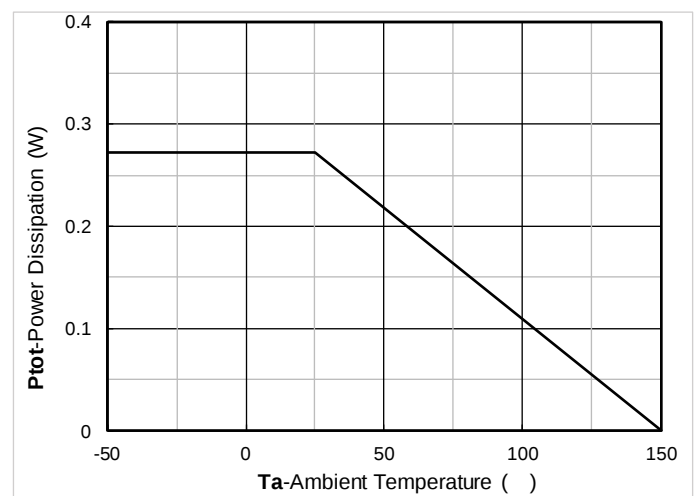


Figure 12. Power dissipation

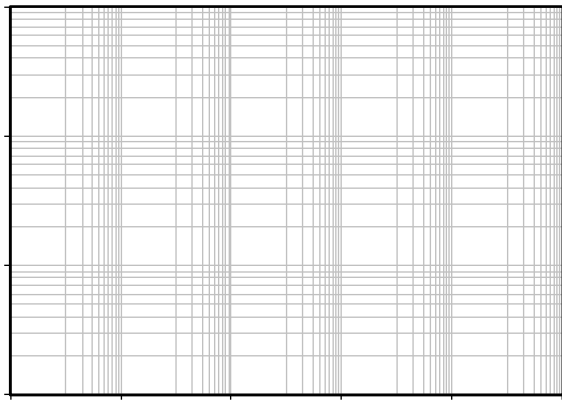


Figure 13. Maximum Transient Thermal Impedance

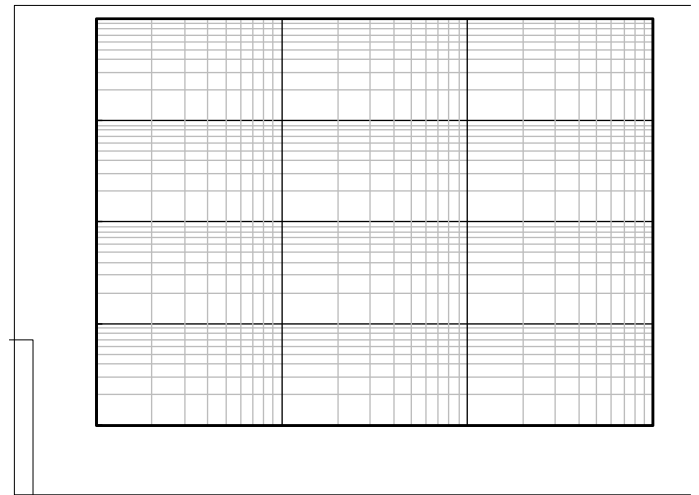


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

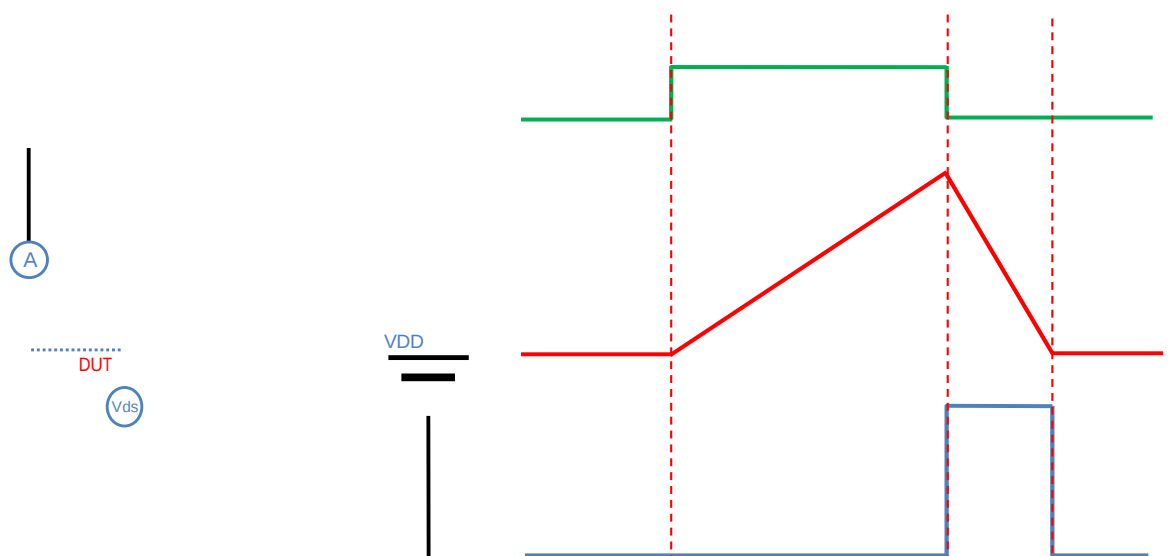


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



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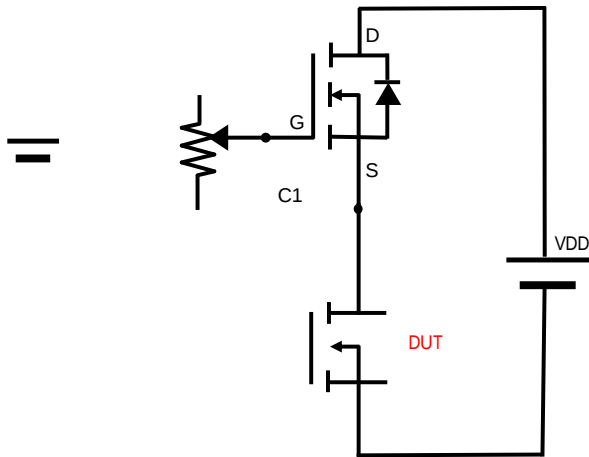


Figure B. Gate Charge Test Circuit & Waveform

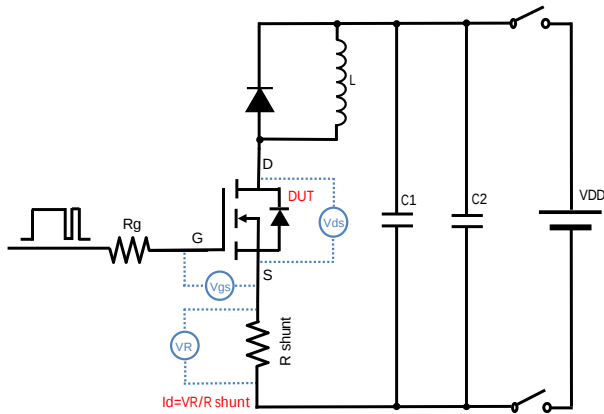


Figure C. Resistive Switching Test Circuit & Waveform

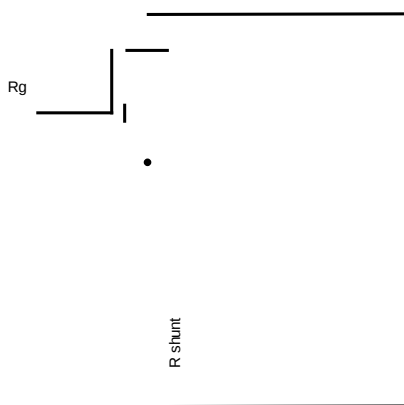


Figure D. Diode Recovery Test Circuit & Waveform

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